



CSP MOSFET 数据手册

NP12023ECA

CSP 12V Typ 2.3m Ω Dual N-Channel MOSFET

Rev. 1.2

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最大额定值 Maximum Ratings^①

参数 Parameter	符号 Symbol	数值 Value	单位 Unit
源极-源极击穿电压 Source-Source Breakdown Voltage	BV_{SSS}	12	V
栅极-源极电压 Gate to Source Voltage	V_{GS}	± 8	V
直流源极电流 Source Current (DC)	I_S	13.5	A
脉冲源电极电流 Source Current (Pulse) $PW \leq 10\mu s, Duty\ Cycle \leq 1\%$	I_{Sp}	135	A
耗散功率 Power Dissipation	P_D	0.54	W
结温 Operating Junction Temperature	T_J	-55...+150	$^{\circ}C$
存储温度 Storage Temperature	T_{stg}	-55...+150	$^{\circ}C$

① 超过最大额定值表中列出的使用条件可能会损坏芯片。如果超过这些限制值中的任何一个，则芯片的功能可能无法保证，芯片可能发生损坏并影响可靠性。

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

热阻特性 Thermal Resistance^②

参数 Parameter	符号 Symbol	数值 (最大) Max. Value	单位 Unit
结到环境热阻 Thermal Resistance Junction to Ambient	$R_{\theta JA}$	231	$^{\circ}C/W$

② 芯片表面贴于 70mmX70mm 环氧树脂 PCB 板。

Surface mounted on Mounted on 70mmx70mm FR4 board

电气特性 Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

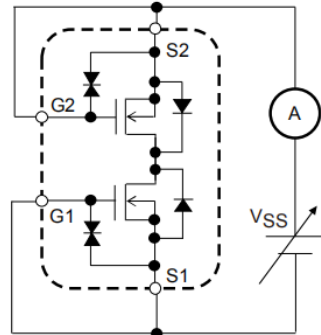
项目③ Parameter	符号 Symbol	测试条件 Conditions	数值 Value			单位 Unit
			Min.	Typ.	Max.	
源极-源极击穿电压 Source to Source Breakdown Voltage	$V_{(BR)SSS}$	$I_S = 1\text{ mA}$, $V_{GS} = 0\text{ V}$ Test Circuit 1	12	-	-	V
零栅压下源极漏电流 Zero Gate Voltage Source Current	I_{SSS}	$V_{SS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$ Test Circuit 1	-	-	1.0	μA
栅极-源极漏电流 Gate to Source Leakage Current	I_{GSS1}	$V_{GS} = \pm 5\text{ V}$, $V_{SS} = 0\text{ V}$ Test Circuit 2	-	-	± 1.5	μA
栅极-源极漏电流 Gate to Source Leakage Current	I_{GSS2}	$V_{GS} = \pm 8\text{ V}$, $V_{SS} = 0\text{ V}$ Test Circuit 2	-	-	± 10	μA
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{SS} = 6\text{ V}$, $I_S = 1\text{ mA}$ Test Circuit 3	0.4	-	1.0	V
源极到源极直流导通电阻 Static Source to Source On-State Resistance	$R_{SS(on)}$	$I_S = 5\text{ A}$, $V_{GS} = 4.5\text{ V}$ Test Circuit 4	1.6	2.3	3.2	$\text{m}\Omega$
		$I_S = 5\text{ A}$, $V_{GS} = 3.8\text{ V}$ Test Circuit 4	1.7	2.7	3.4	$\text{m}\Omega$
		$I_S = 5\text{ A}$, $V_{GS} = 3.1\text{ V}$ Test Circuit 4	1.8	3.2	4.6	$\text{m}\Omega$
		$I_S = 5\text{ A}$, $V_{GS} = 2.5\text{ V}$ Test Circuit 4	2	3.9	6.6	$\text{m}\Omega$
源极到源极正向压降 Forward Source to Source Voltage	$V_{F(S-S)}$	$I_S = 1\text{ A}$, $V_{GS} = 0$ Test Circuit 7	0.4	0.58	1.0	V
栅极电阻 Gate Resistance	R_g	$f = 1\text{ MHz}$		1400		Ω

③ 产品的参数性能按照上述表格参数所描述，除非有额外的说明。如果产品工作在其他不同的条件下，产品的电学性能可能并不遵守上述参数。

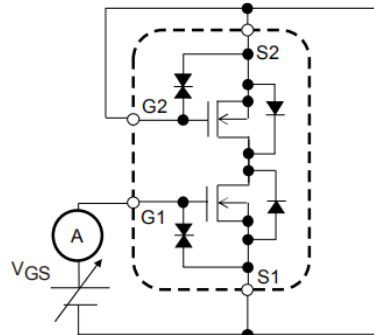
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

测试电路范例 Test Circuits Example

Test Circuit 1
VSSS / ISSS

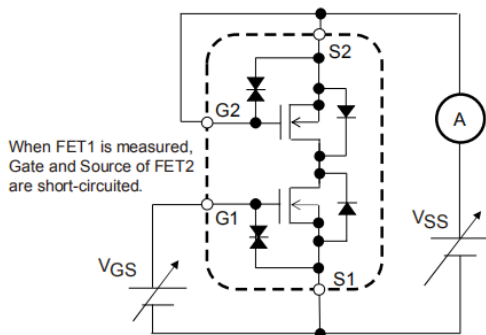


Test Circuit 2
IGSS



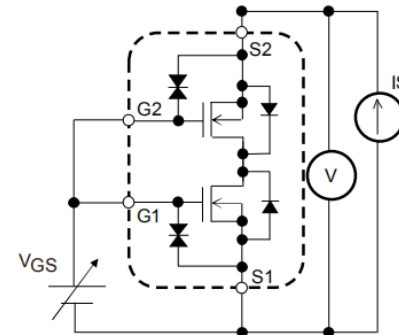
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 3
VGS(th)

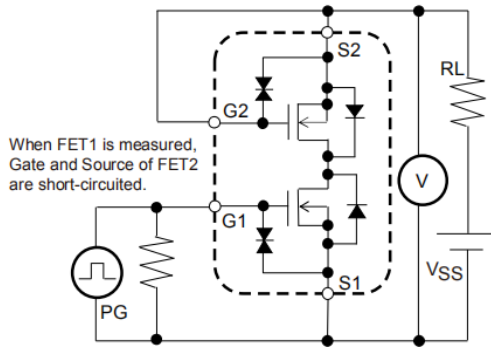


When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 4
RSS(on)

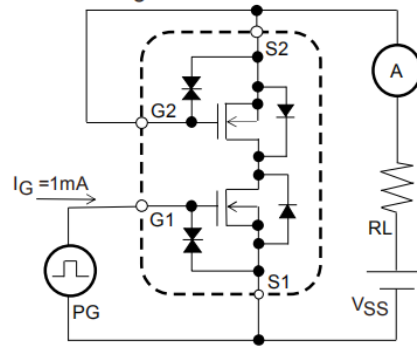


Test Circuit 5
 $t_d(on)$, t_r , $t_d(off)$, t_f



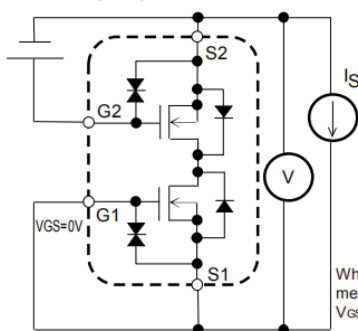
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 6
Qg



When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 7
VF(S-S)



When FET1 is measured, +4.5V is added to VGS of FET2.

特征电学和温度曲线 Typical Electrical and Thermal Characteristics

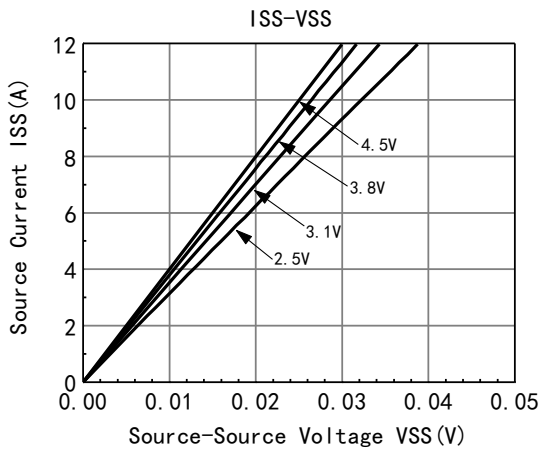


Figure 1: On-Region Characteristics

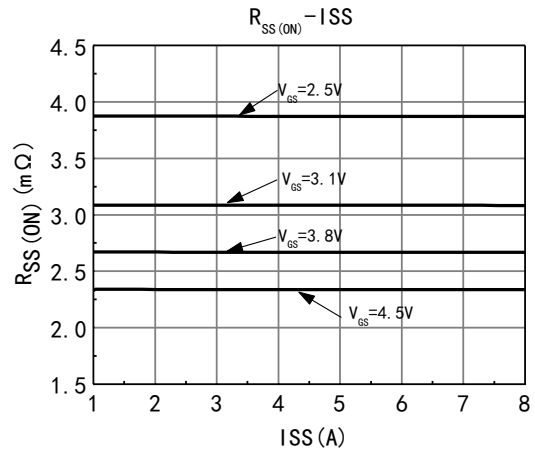


Figure 2: On-Resistance vs. Source Current and Gate Voltage

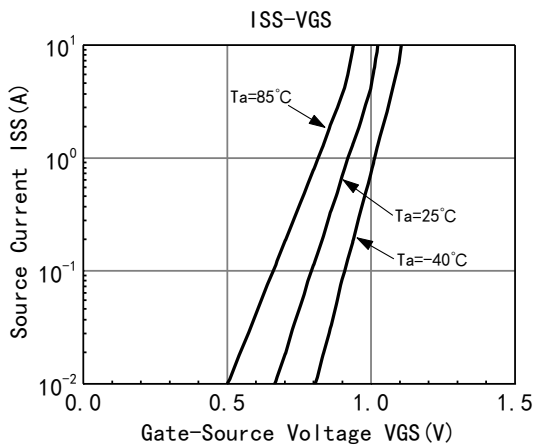


Figure 3: Typical Transfer Characteristics

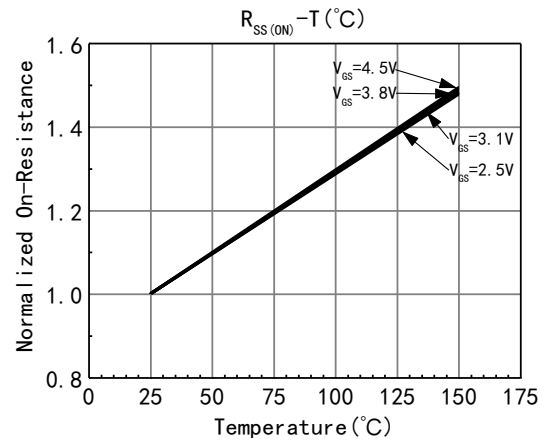


Figure 4: On-Resistance vs. Junction Temperature

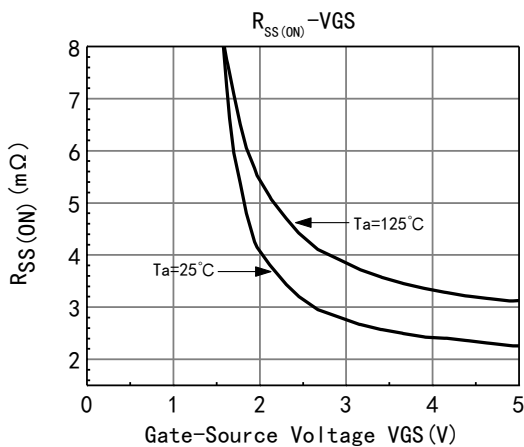


Figure 5: On-Resistance vs. Gate-Source Voltage

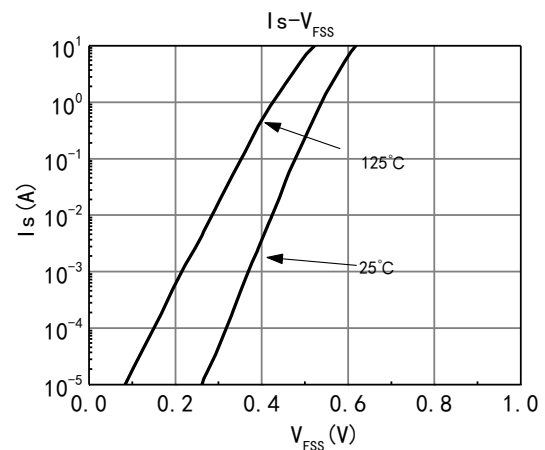


Figure 6: Forward Source to Source Characteristics

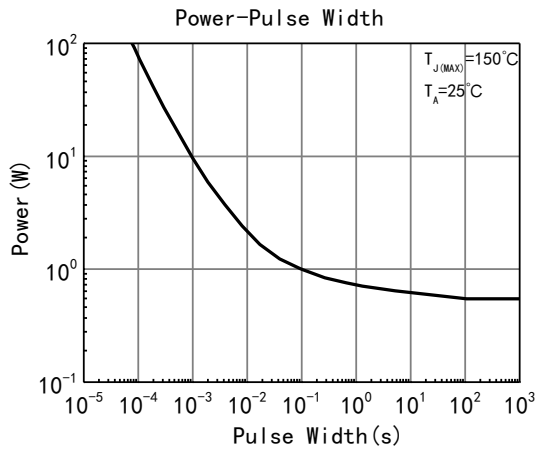


Figure 7: Single Pulse Power Rating Junction to Ambient

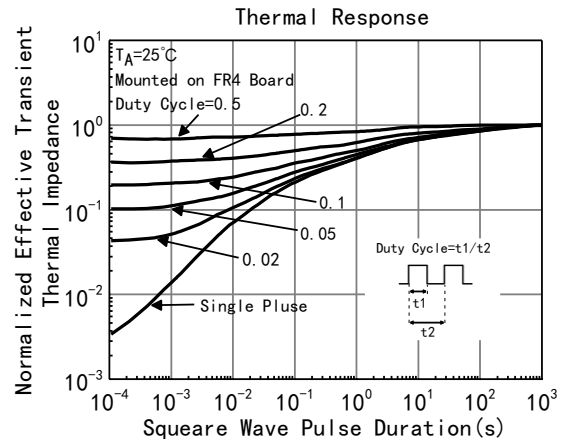


Figure 8: Normalized Maximum Transient Thermal Impedance

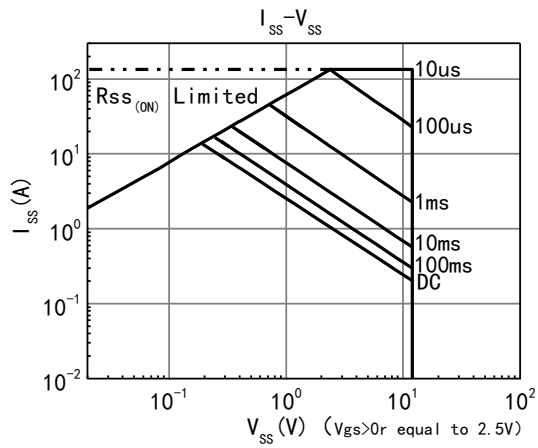
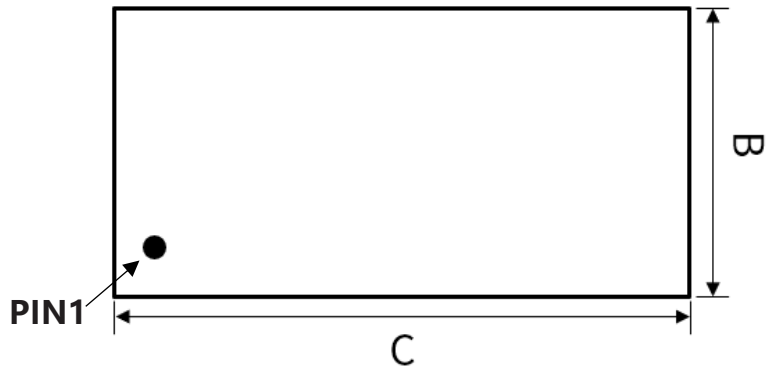


Figure 9: Safe Operating Area

封装尺寸 Package Dimensions:

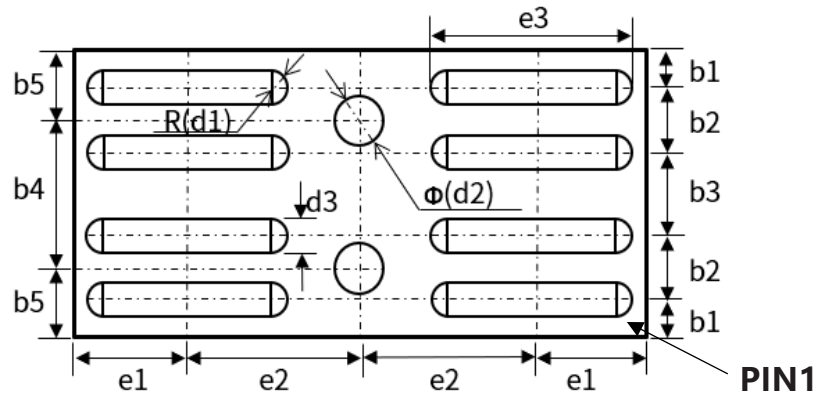
Top View



Side View



Bottom View



Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.27	0.30	0.33	0.0106	0.0118	0.0130
B	1.45	1.50	1.55	0.0571	0.0591	0.0610
C	2.94	3.00	3.06	0.1157	0.1181	0.1205
b1	0.1925	0.2125	0.2325	0.0076	0.0084	0.0092
b2	0.295	0.325	0.355	0.0116	0.0128	0.0140
b3	0.395	0.425	0.455	0.0156	0.0167	0.0179
b4	0.70	0.75	0.80	0.0276	0.0295	0.0315
b5	0.345	0.375	0.405	0.0136	0.0148	0.0159
d1	0.0825	0.0875	0.0925	0.0032	0.0034	0.0036
d2	0.23	0.25	0.27	0.0091	0.0098	0.0106
d3	0.155	0.175	0.195	0.0061	0.0069	0.0077
e1	0.555	0.605	0.655	0.0219	0.0238	0.0258
e2	0.845	0.895	0.945	0.0333	0.0352	0.0372
e3	0.99	1.04	1.09	0.0390	0.0409	0.0429

历史版本 Version history

版本号	时间	修改内容
V1.0	2021 年 12 月	初始版本
V1.1	2022 年 01 月	新版规格书更新参数和曲线
V1.2	2022 年 05 月	增加包装信息